

IN THE CLAIMS

Please amend the claims as follows:

1-4. (Canceled)

5. (Previously Presented) An apparatus for processing a substrate, the apparatus comprising:

- (a) a chamber; and
- (b) a high capacity pump abutting the chamber, the pump having an inlet connected to the chamber to rapidly evacuate gas in the chamber and an outlet that exhausts the evacuated gas to atmospheric pressure.

6-21. (Canceled)

22. (Previously Presented) An apparatus for processing a substrate, the apparatus comprising:

- (a) a process chamber comprising a support and a gas distributor; and
- (b) a high capacity pumping system comprising a pre-vacuum pump abutting the process chamber, the pre-vacuum pump having an inlet connected to the process chamber to evacuate gas from the process chamber and an outlet that exhausts the evacuated process gas to atmospheric pressure, whereby a substrate held on the support is processed by process gas introduced through the gas distributor into the process chamber.

23-29. (Canceled)

30. (Previously Presented) An apparatus for processing a substrate, the apparatus comprising a chamber, a pump abutting the chamber and capable of operating at different speeds, a pump controller to control the speed of the pump, and a pressure controller to control a gas pressure of a gas in the chamber by providing a signal in relation to the gas pressure to the pump controller that changes the speed of

Page 2

325657_1

the pump in relation to the signal from a first pump speed at which the gas in the chamber is evacuated at a first volumetric flow rate to a second pump speed at which the gas in the chamber is evacuated at a second volumetric flow rate.

31-41. (Canceled)

42. (Previously Presented) An apparatus for processing a substrate, the apparatus comprising a pump having a plurality of inlet ports, a first inlet port provided to evacuate gas from a first chamber or first pump, and a second inlet port provided to evacuate gas from a second chamber or second pump, the pump abutting at least one of the chambers.

43-49. (Canceled)

50. (Previously Presented) An apparatus for processing a substrate, the apparatus comprising a multiple inlet pump having a first inlet port in a first inlet stage, and a second inlet port in a second inlet stage, the first inlet port provided to evacuate gas from a first chamber or first pump, and a second inlet port provided to evacuate gas from a second chamber or second pump, the multiple inlet pump abutting at least one of the chambers.

51-58. (Canceled)

59. (Previously Presented) An apparatus for processing a substrate, the apparatus comprising:

(a) a plurality of chambers that are shaped and sized to hold one or more substrates; and

(b) a pump having a first inlet port in a first inlet stage, and a second inlet port in a second inlet stage, the first inlet port provided to evacuate gas from one chamber and a second inlet port provided to evacuate gas from another chamber, the pump abutting at least one of the chambers.

60-107. (Canceled)

108. (Previously Presented) An apparatus for processing a substrate, the apparatus comprising:

- (a) a chamber capable of holding a substrate and processing the substrate in a gas;
- (b) a pump capable of evacuating a gas from the chamber, the pump abutting the chamber and capable of changing its speed; and
- (c) a pump controller adapted to provide a signal to the pump to vary the speed of the pump from a first pump speed at which the gas in the chamber is evacuated at a first volumetric flow rate to a second pump speed at which the gas in the chamber is evacuated at a second volumetric flow rate to control the rates of evacuation of the gas in the chamber to reduce condensation of moisture in the chamber.

109. (Previously Presented) An apparatus for processing a substrate, the apparatus comprising:

- (a) a chamber capable of holding a substrate and processing the substrate in a gas;
- (b) a pump capable of evacuating a gas from the chamber, the pump abutting the chamber and being capable of operating at different speeds; and
- (c) means for changing a speed of the pump from a first pump speed at which the gas in the chamber is evacuated at a first volumetric flow rate to a second pump speed at which the gas in the chamber is evacuated at a second volumetric flow rate to control the rates of evacuation of the gas to reduce condensation of moisture in the chamber.

110. (Previously Presented) An apparatus for processing a substrate, the apparatus comprising:

- a chamber; and

a pump abutting the chamber, the pump having an inlet connected to the chamber to evacuate gas in the chamber and an outlet that exhausts the evacuated gas to atmospheric pressure, the apparatus further comprising a pressure controller to control the pressure of the gas in the chamber by adjusting a speed of the pump.

111. (Previously Presented) An apparatus for processing a substrate, the apparatus comprising:

a load-lock chamber comprising an enclosure; and

a pump abutting the load-lock chamber, the pump having an inlet connected to the load-lock chamber to evacuate gas from the load-lock chamber and an outlet that exhausts the gas to atmospheric pressure, the apparatus further including a pressure controller to control the pressure of the gas in the load-lock chamber by adjusting a speed of the pump.

112. (Previously Presented) An apparatus for processing a substrate, the apparatus comprising:

a process chamber comprising a support and a gas distributor; and

a pump system comprising a pre-vacuum pump abutting the process chamber, the pre-vacuum pump having an inlet connected to the process chamber to evacuate gas from the process chamber and an outlet that exhausts the evacuated process gas to atmospheric pressure, whereby a substrate held on the support is processed by process gas introduced through the gas distributor into the process chamber, the apparatus further including a pressure controller to control the pressure of the processed gas in the process chamber by adjusting a speed of the pre-vacuum pump.